

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE6080A uses advanced trench technology and design to provide excellent $R_{\text{DS}(\text{ON})}$ with low gate charge. It can be used in a wide variety of applications.

General Features

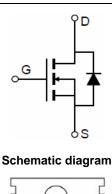
- V_{DS} =60V,I_D =80A $R_{DS(ON)}$ =6.5m Ω (typical) @ V_{GS} =10V $R_{DS(ON)}$ =7.5m Ω (typical) @ V_{GS} =4.5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

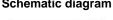
Application

- PWM
- Load Switching

100% UIS TESTED!

100% AVds TESTED!







Marking and pin assignment



TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE6080A	NCE6080A	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	80	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	56.5	Α
Pulsed Drain Current	I _{DM}	320	Α
Maximum Power Dissipation	P _D	110	W
Derating factor		0.73	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	390	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 175	°C



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Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	R _{eJC}	1.36	°C/W
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Electrical Characteristics (T_C=25 °C unless otherwise noted)

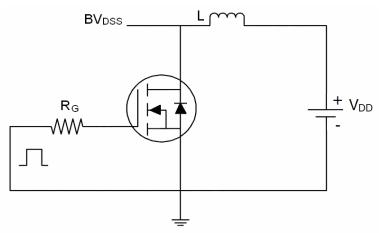
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	<u>.</u>					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	<u>.</u>					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.8	1.3	1.8	V
Drain Course On Ctate Desistance	Б	V _{GS} =10V, I _D =20A	-	6.5	8.0	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =20A	-	7.5	9.5	mΩ
Forward Transconductance	g Fs	V _{DS} =5V,I _D =20A	20	-	-	S
Dynamic Characteristics (Note4)	<u>.</u>					
Input Capacitance	C _{lss}	\/ -20\/\/ -0\/	-	4000	-	PF
Output Capacitance	Coss	V_{DS} =30V, V_{GS} =0V, F=1.0MHz	-	290	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0WIFIZ	-	210	-	PF
Switching Characteristics (Note 4)	<u>.</u>					
Turn-on Delay Time	t _{d(on)}		-	8.5	-	nS
Turn-on Rise Time	t _r	V_{DD} =30V, R_L =1 Ω	-	7	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	40	-	nS
Turn-Off Fall Time	t _f		-	15	-	nS
Total Gate Charge	Qg	V -20VI -20A	-	90.3		nC
Gate-Source Charge	Q _{gs}	$V_{DS}=30V,I_{D}=20A,$ $V_{GS}=10V$	-	10.9		nC
Gate-Drain Charge	Q _{gd}	V _{GS} -10V	-	20.6		nC
Drain-Source Diode Characteristics	·					
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	80	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 20A	-	32	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	45	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

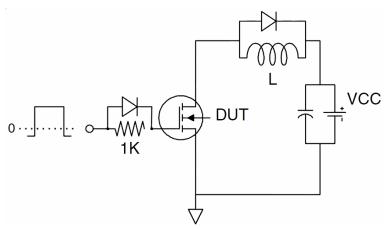
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. E_{AS} condition : $Tj{=}25\,^{\circ}\!\mathrm{C}$, $V_{DD}{=}30V$, $V_{G}{=}10V$, $L{=}0.5mH$, $Rg{=}25\Omega$

Test circuit

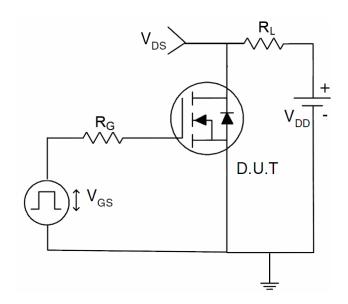
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

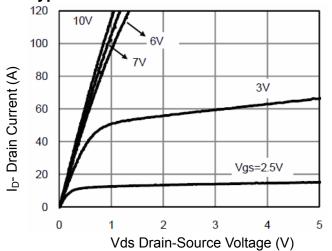


Figure 1 Output Characteristics

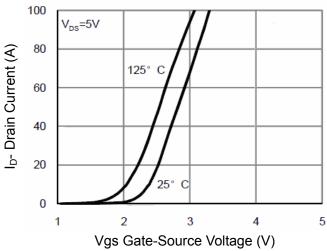


Figure 2 Transfer Characteristics

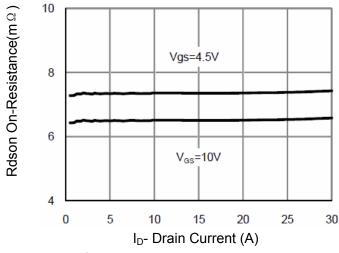


Figure 3 Rdson- Drain Current

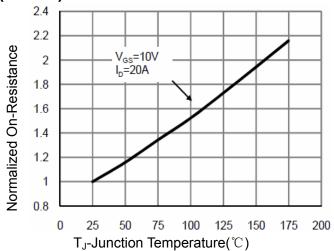


Figure 4 Rdson-JunctionTemperature

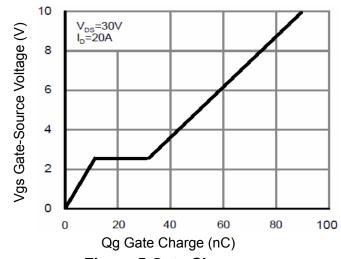


Figure 5 Gate Charge

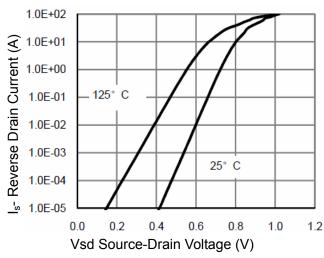


Figure 6 Source- Drain Diode Forward

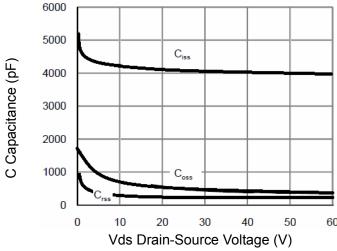


Figure 7 Capacitance vs Vds

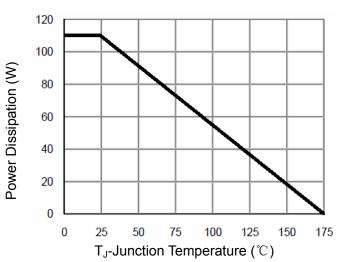


Figure 9 Power De-rating

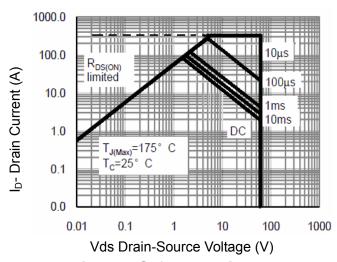


Figure 8 Safe Operation Area

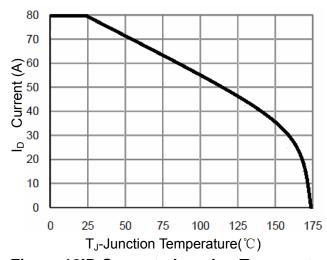
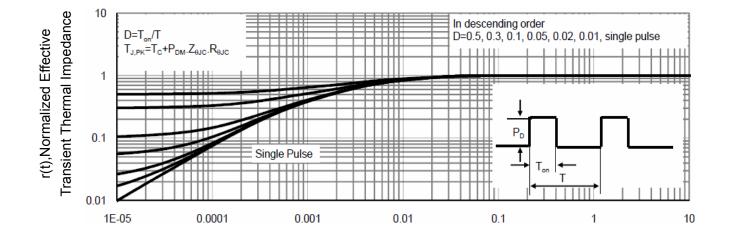


Figure 10ID Current- Junction Temperature

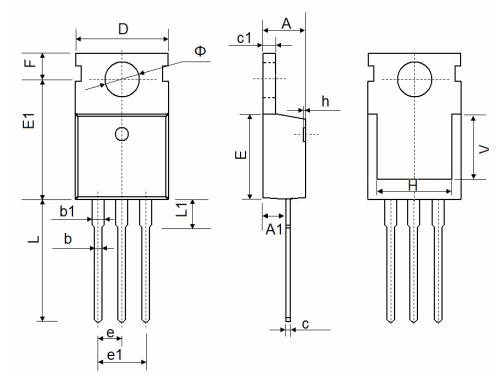


Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance





TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	



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